

isc Silicon NPN Darlington Power Transistor

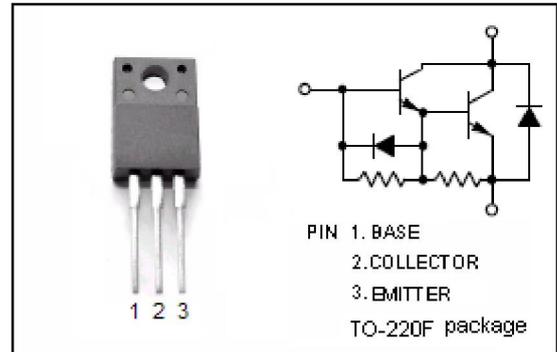
BU807FI

DESCRIPTION

- High Voltage: $V_{CBO} = 330V(\text{Min})$
- Low Saturation Voltage-
: $V_{CE(\text{sat})} = 1.5V(\text{Max}) @ I_C = 5A$

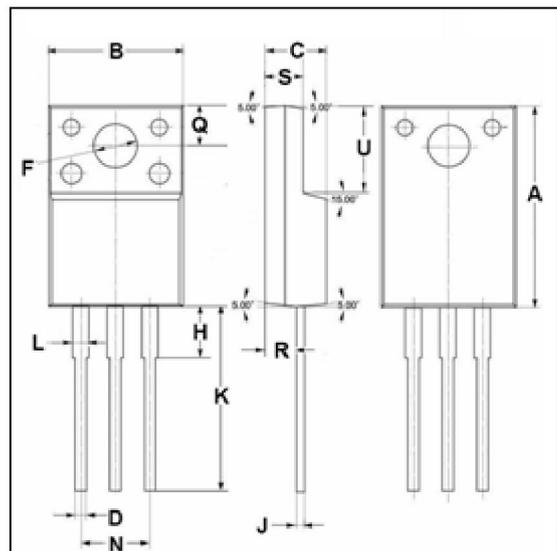
APPLICATIONS

- Designed for use in horizontal deflection circuits in TV's and CRT's.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	330	V
V_{CEV}	Collector-Emitter Voltage	330	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	8	A
I_{CM}	Collector Current-Peak	15	A
I_B	Base Current	2	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	30	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.80
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.85
U	6.40	6.60

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=100\text{mA}; I_B=0$	150			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=50\text{mA}$			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=5\text{A}; I_B=50\text{mA}$			2.4	V
I_{CES}	Collector Cutoff Current	$V_{CE}=330\text{V}; V_{BE}=0$			0.1	mA
I_{CEV}	Collector Cutoff Current	$V_{CE}=330\text{V}; V_{BE(off)}=6\text{V}$			0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=6\text{V}; I_C=0$			3.0	mA
V_{ECF}	C-E Diode Forward Voltage	$I_F=4\text{A}$			2.0	V